

Prospective Data  
**Insulated Gate Bi-Polar Transistor**  
Type T1200TB25A

**Absolute Maximum Ratings**

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
$V_{CES}$	Collector – emitter voltage	2500	V
$V_{DC\ link}$	Permanent DC voltage for 100 FIT failure rate.	1250	V
$V_{GES}$	Peak gate – emitter voltage	$\pm 20$	V

	RATINGS	MAXIMUM LIMITS	UNITS
$I_{C(DC)}$	DC collector current, IGBT	1200	A
$I_{CRM}$	Repetitive peak collector current, $t_p=1ms$ , IGBT	2400	A
$I_{F(DC)}$	Continuous DC forward current, Diode	1200	A
$I_{FRM}$	Repetitive peak forward current, $t_p=1ms$ , Diode	2400	A
$I_{FSM}$	Peak non-repetitive surge $t_p=10ms$ , $V_{RM}=60\%V_{RRM}$ , Diode (Note 4)	7120	A
$I_{FSM2}$	Peak non-repetitive surge $t_p=10ms$ , $V_{RM}\leq 10V$ , Diode (Note 4)	7830	A
$P_{MAX}$	Maximum power dissipation, IGBT (Note 2)	5.9	KW
$(di/dt)_{cr}$	Critical diode di/dt (note 3)	3000	A/ $\mu s$
$T_j$	Operating temperature range.	-40 to +125	$^{\circ}C$
$T_{stg}$	Storage temperature range.	-40 to +125	$^{\circ}C$

Notes: -

- 1) Unless otherwise indicated  $T_j = 125^{\circ}C$ .
- 2)  $T_{sink} = 25^{\circ}C$ , double side cooled.
- 3) Maximum commutation loop inductance 200nH.
- 4) Half-sinewave,  $125^{\circ}C$   $T_j$  initial.

## Characteristics

### IGBT Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V <sub>CE(sat)</sub>	Collector – emitter saturation voltage	-	2.15	2.45	I <sub>C</sub> = 1200A, V <sub>GE</sub> = 15V, T <sub>j</sub> = 25°C	V
		-	3.0	3.30	I <sub>C</sub> = 1200A, V <sub>GE</sub> = 15V	V
V <sub>T0</sub>	Threshold voltage	-	-	1.30	Current range: 400 – 1200A	V
r <sub>T</sub>	Slope resistance	-	-	1.67		mΩ
V <sub>GE(TH)</sub>	Gate threshold voltage	-	5.8	6.3	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 100mA	V
I <sub>CES</sub>	Collector – emitter cut-off current	-	10	30	V <sub>CE</sub> = V <sub>CES</sub> , V <sub>GE</sub> = 0V	mA
I <sub>GES</sub>	Gate leakage current	-	5	±20	V <sub>GE</sub> = ±20V	μA
C <sub>ies</sub>	Input capacitance	-	150	-	V <sub>CE</sub> = 25V, V <sub>GE</sub> = 0V, f = 1MHz	nF
t <sub>d(on)</sub>	Turn-on delay time	-	1.0	-	I <sub>C</sub> = 1200A, V <sub>CE</sub> = 1250V, di/dt = 2000A/μs	μs
t <sub>r(V)</sub>	Rise time	-	2.5	-		μs
Q <sub>g(on)</sub>	Turn-on gate charge	-	8.5	-	V <sub>GE</sub> = ±15V, L <sub>s</sub> = 200nH	μC
E <sub>on</sub>	Turn-on energy	-	2.8	-	R <sub>g(ON)</sub> = 2.2Ω, R <sub>g(OFF)</sub> = 5.1Ω, C <sub>GE</sub> = 100nF	J
t <sub>d(off)</sub>	Turn-off delay time	-	1.5	-	Integral diode used as freewheel diode (Note 3 & 4)	μs
t <sub>f(I)</sub>	Fall time	-	8.3	-		μs
Q <sub>g(off)</sub>	Turn-off gate charge	-	8	-		μC
E <sub>off</sub>	Turn-off energy	-	2.0	-		J
I <sub>SC</sub>	Short circuit current	-	3150	-	V <sub>GE</sub> = ±15V, V <sub>CC</sub> = 1250V, V <sub>CEmax</sub> ≤ V <sub>CES</sub> , t <sub>p</sub> ≤ 10μs	A

### Diode Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V <sub>F</sub>	Forward voltage	-	2.25	2.55	I <sub>F</sub> = 1200A, T <sub>j</sub> = 25°C	V
		-	2.50	2.80	I <sub>F</sub> = 1200A	V
V <sub>To</sub>	Threshold voltage	-	-	1.53	Current range 400-1200A	V
r <sub>T</sub>	Slope resistance	-	-	1.06		mΩ
I <sub>rm</sub>	Peak reverse recovery current	-	660	-	I <sub>F</sub> = 1200A, V <sub>GE</sub> = -15V, di/dt = 2000A/μs	A
Q <sub>rr</sub>	Recovered charge	-	950	-		μC
t <sub>rr</sub>	Reverse recovery time, 50% chord	-	1.1	-		μs
E <sub>r</sub>	Reverse recovery energy	-	0.7	-		J

### Thermal Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
R <sub>thJK</sub>	Thermal resistance junction to sink, IGBT	-	-	16.9	Double side cooled	K/kW
		-	-	26.5	Collector side cooled	K/kW
		-	-	49	Emitter side cooled	K/kW
R <sub>thJK</sub>	Thermal resistance junction to sink, Diode	-	-	29.2	Double side cooled	K/kW
		-	-	45.2	Cathode side cooled	K/kW
		-	-	84	Anode side cooled	K/kW
F	Mounting force	15	-	25	Note 2	kN
W <sub>t</sub>	Weight	-	1.2	-		kg

Notes:-

- 1) Unless otherwise indicated T<sub>j</sub> = 125°C.
- 2) Consult application note 2008AN01 for detailed mounting requirements
- 3) C<sub>GE</sub> is additional gate – emitter capacitance added to output of gate drive
- 4) Figures 6 to 9 are obtained using integral diode as freewheeling diode

**Curves**

Figure 1 – Typical collector-emitter saturation voltage characteristics

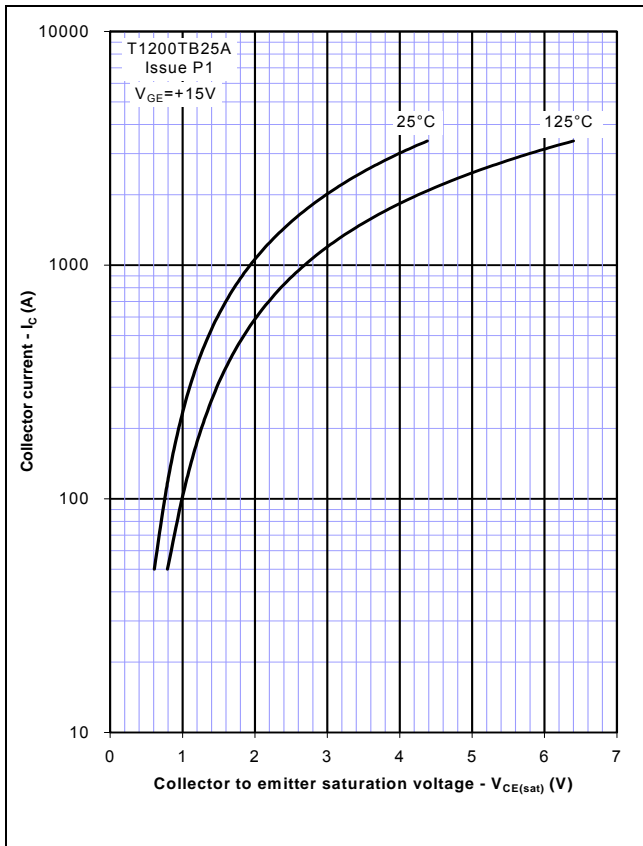


Figure 2 – Typical output characteristic

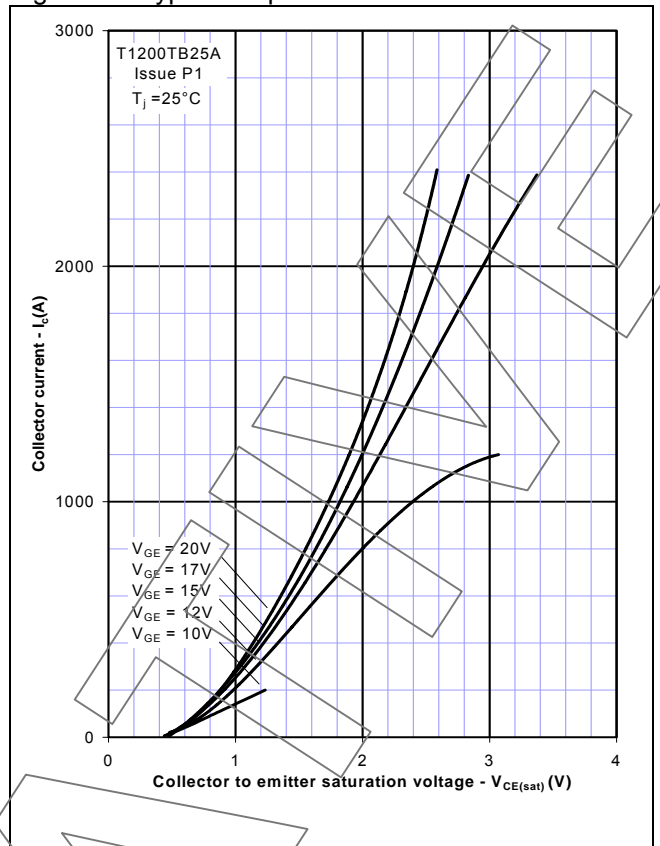


Figure 3 – Typical output characteristic

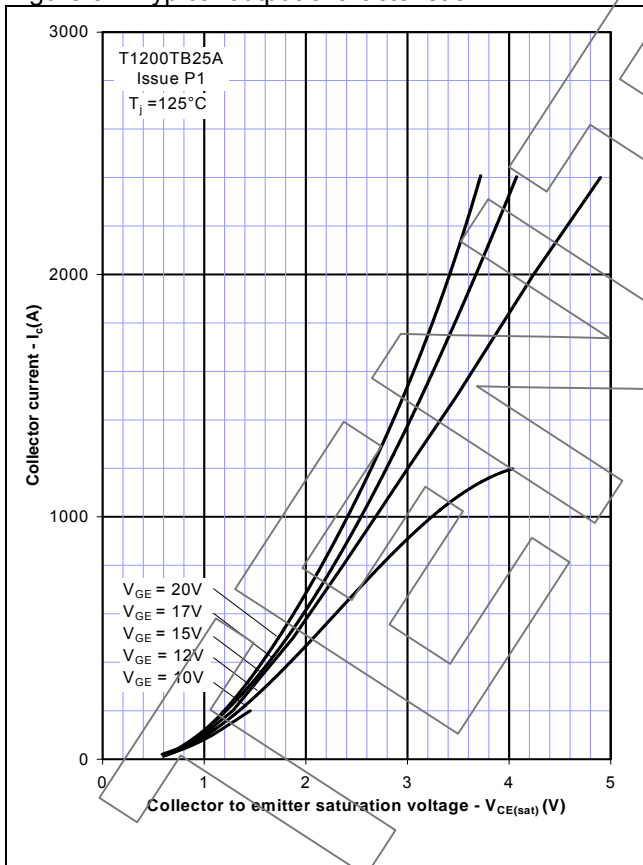


Figure 4 – Typical turn-on delay time vs gate resistance

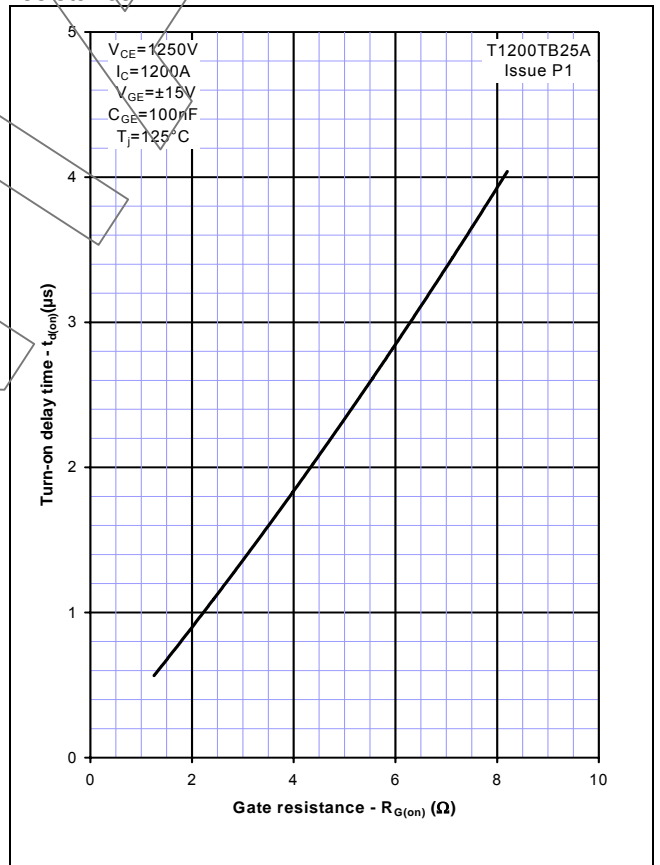


Figure 5 – Typical turn-off delay time vs. gate resistance

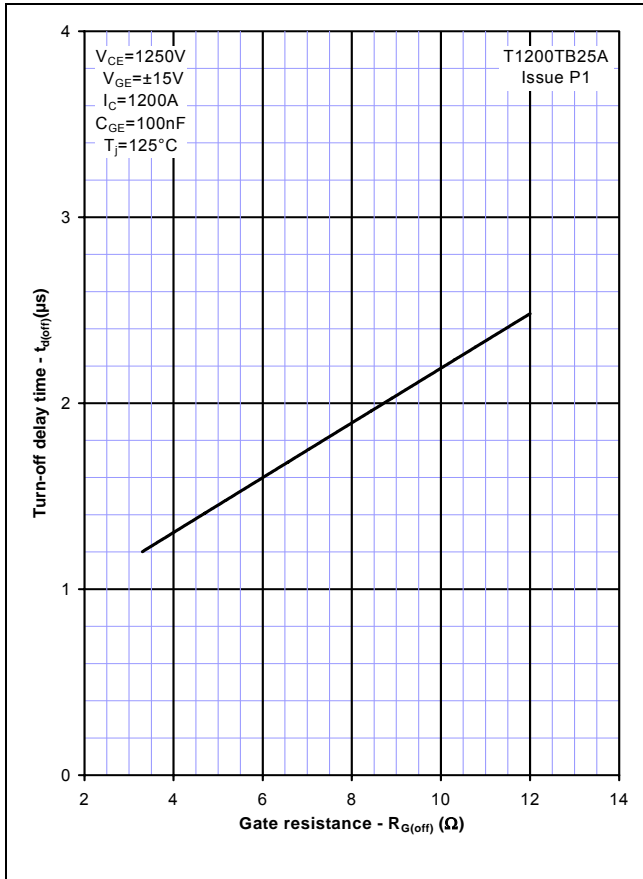


Figure 6 – Typical turn-on energy vs. collector current

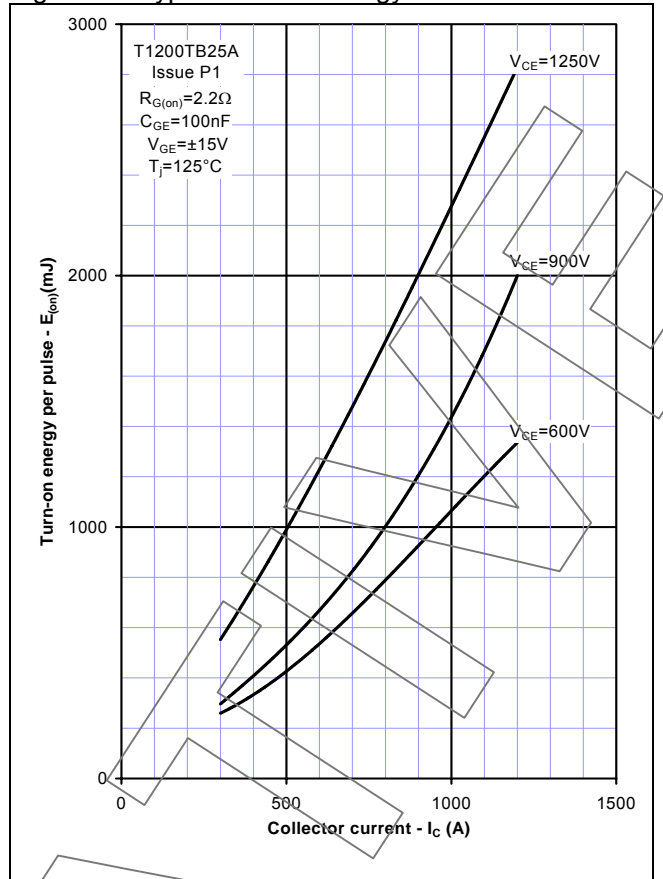


Figure 7 – Typical turn-on energy vs. di/dt

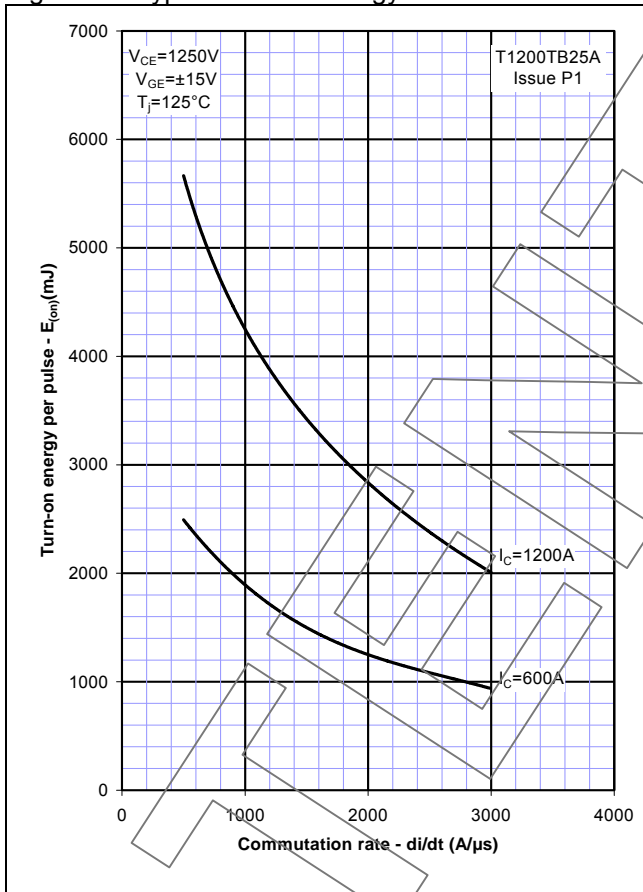


Figure 8 – Typical turn-off energy vs. collector current

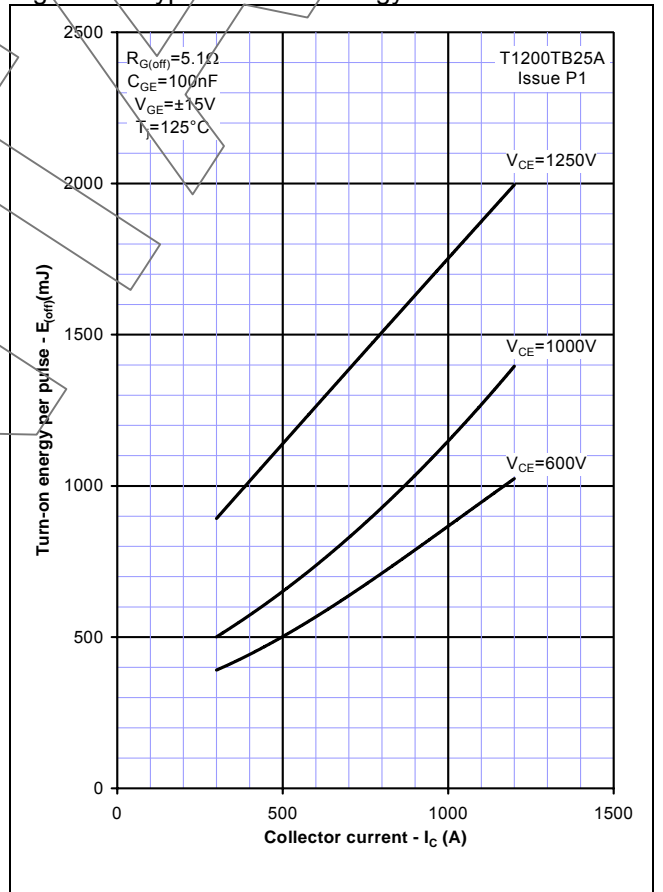


Figure 9 – Turn-off energy vs voltage

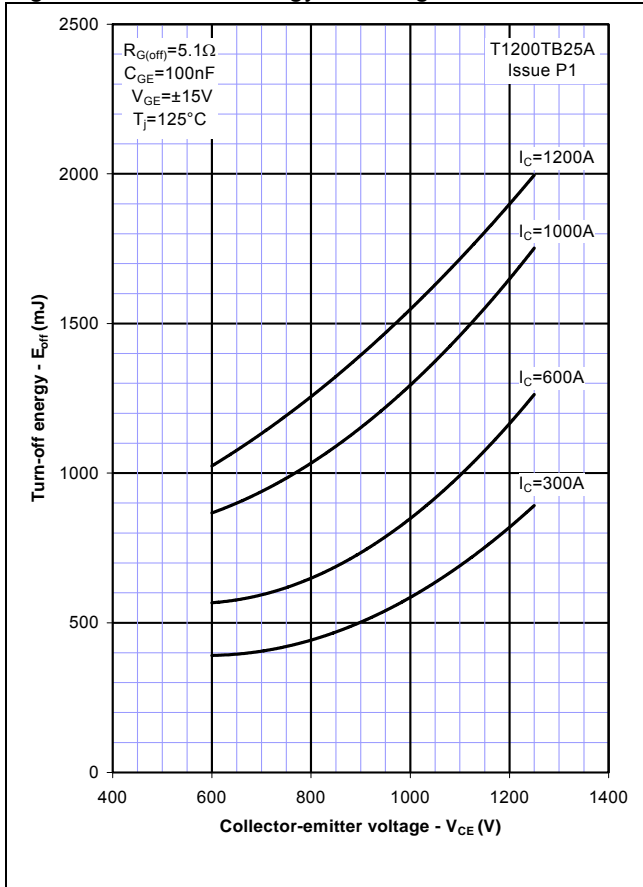


Figure 10 – Safe operating area

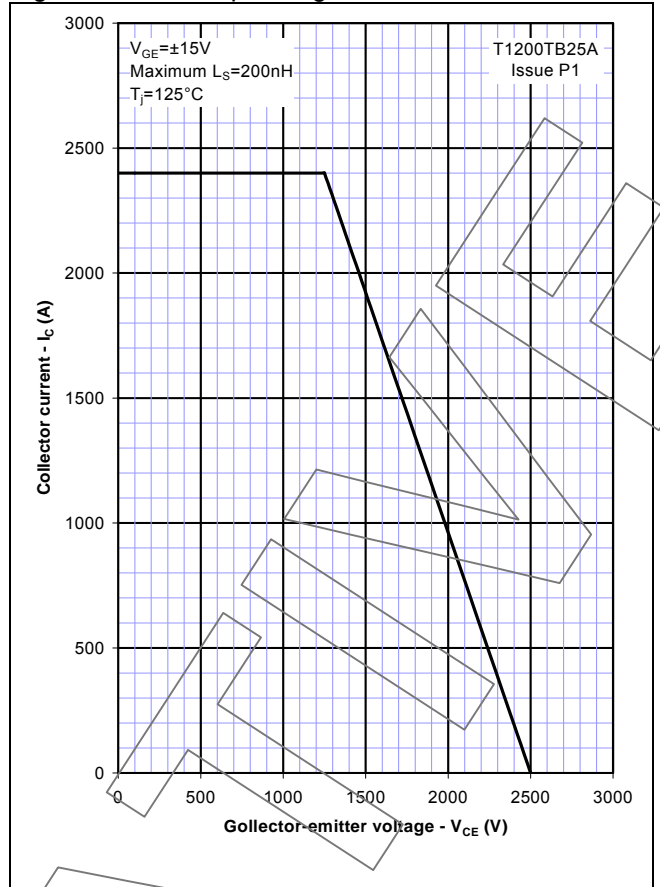


Figure 11 – Typical diode forward characteristics

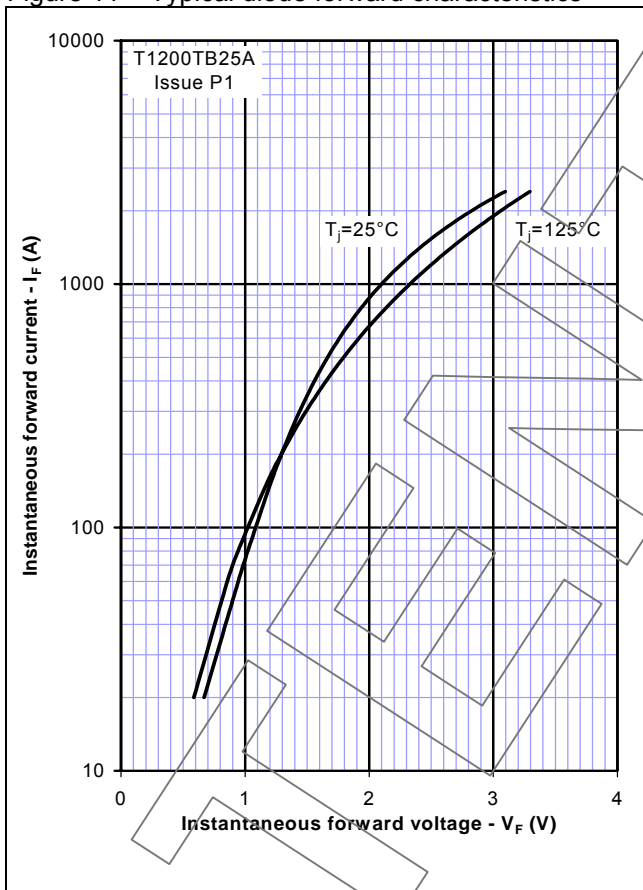


Figure 12 – Typical recovered charge

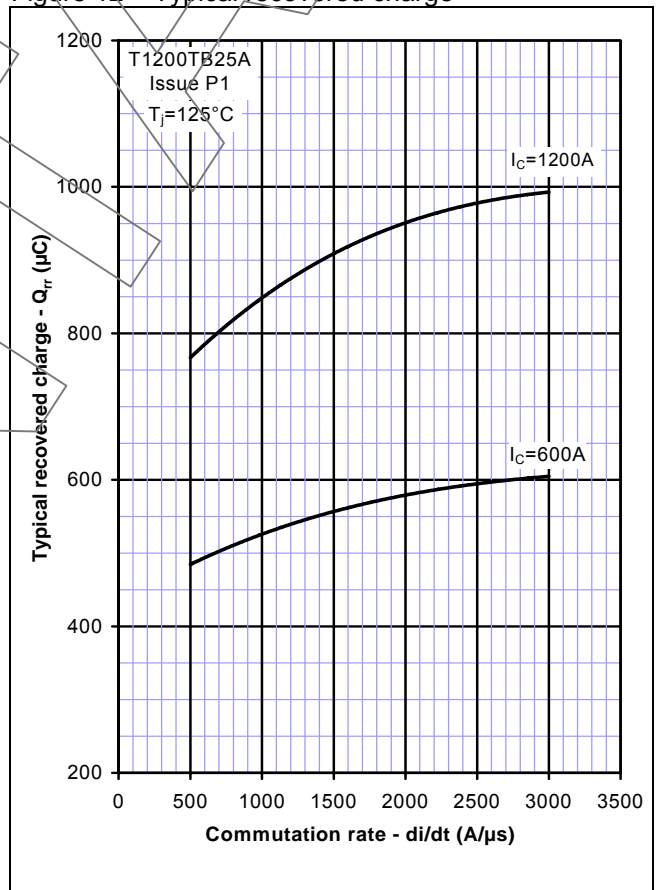


Figure 13 – Typical reverse recovery current

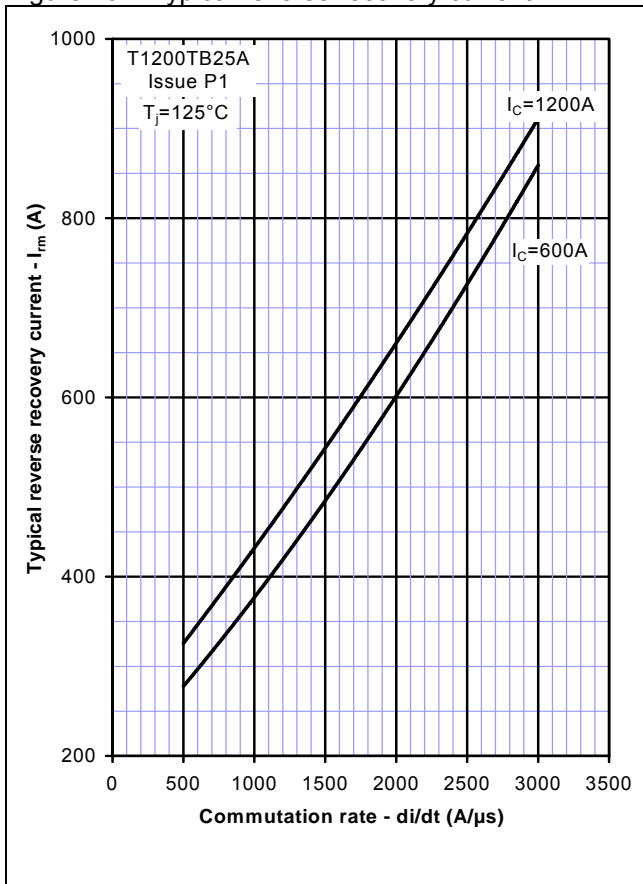


Figure 14 – Typical reverse recovery time

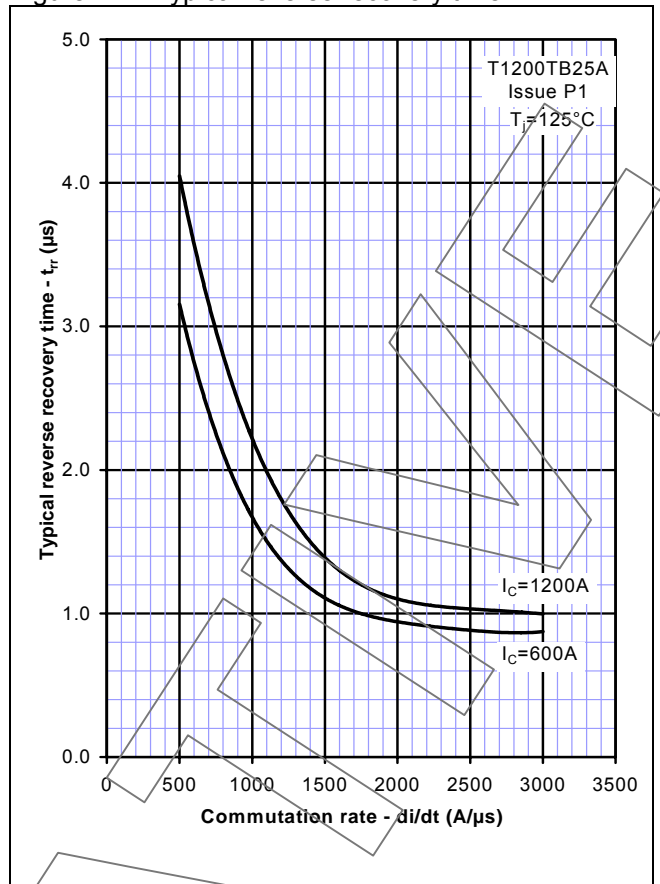


Figure 15 – Transient thermal impedance (IGBT)

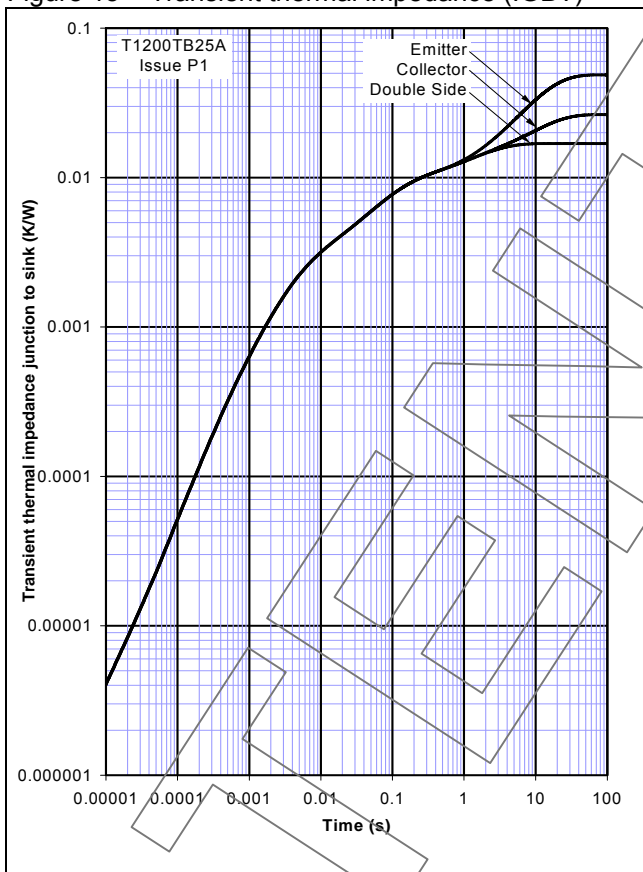
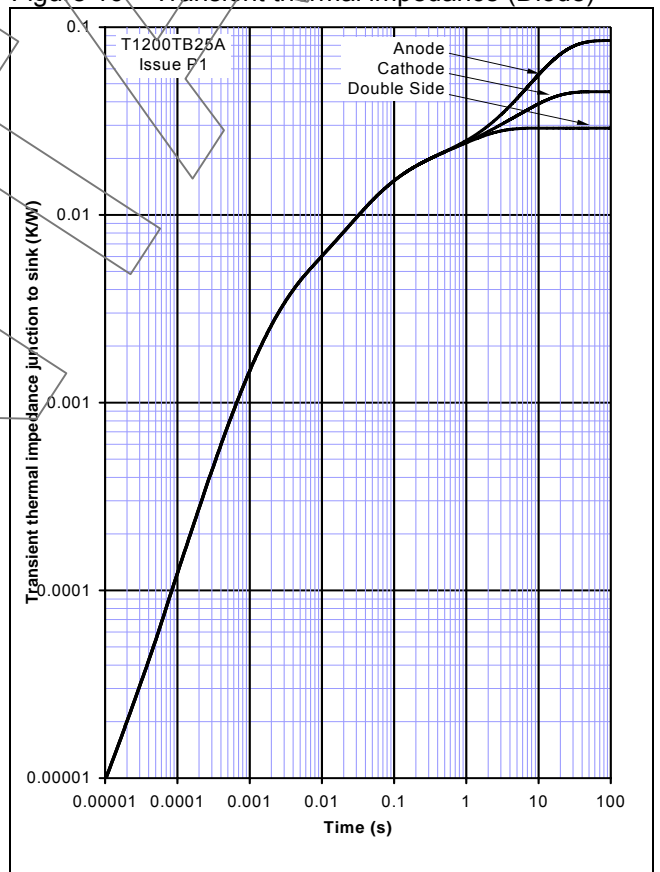
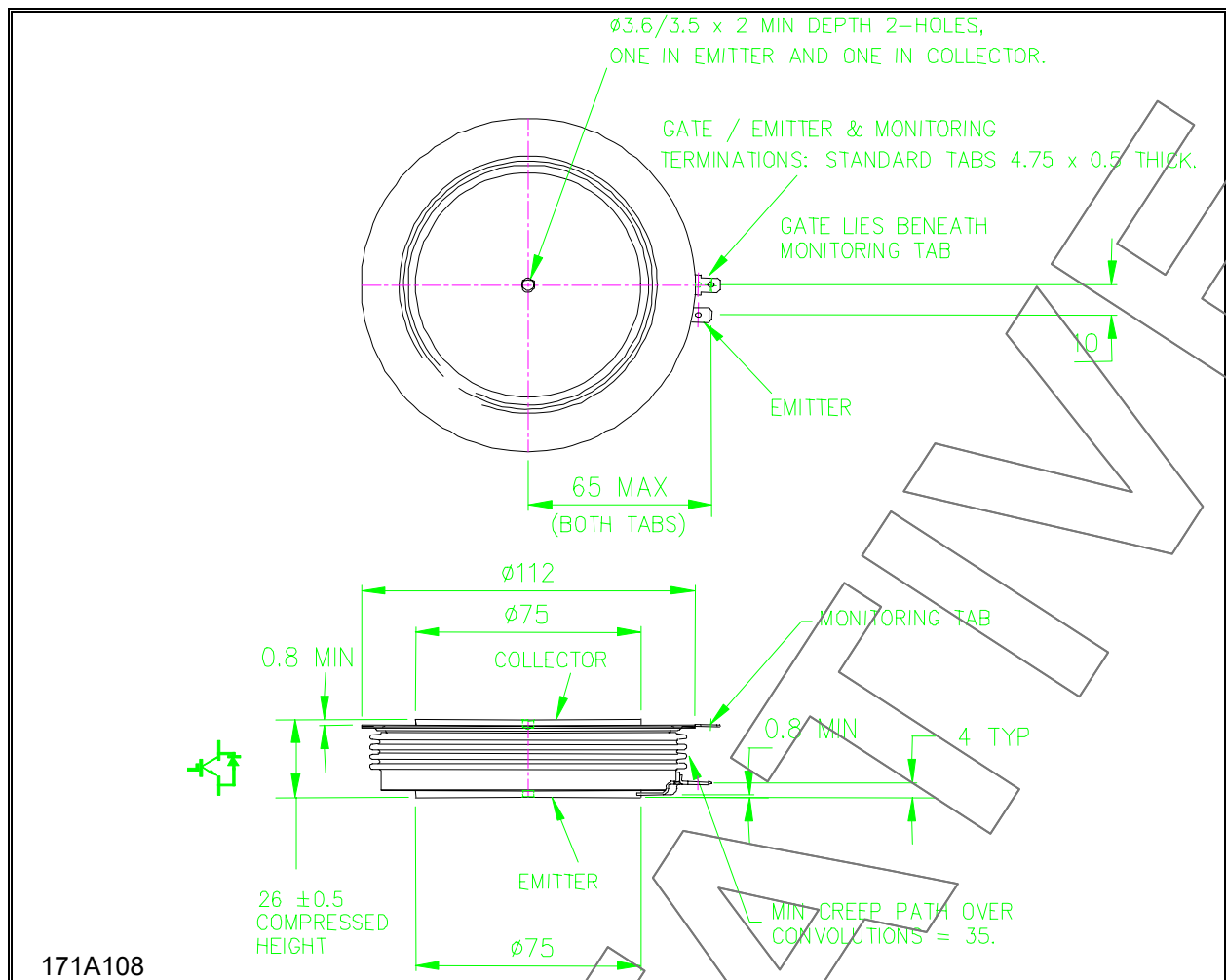


Figure 16 – Transient thermal impedance (Diode)



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(Please quote 10 digit code as below)			
<b>T1200</b>	<b>TB</b>	<b>25</b>	<b>A</b>
Fixed type Code	Fixed Outline Code	Voltage Grade $V_{CES}/100$ 25	Fixed format code
Typical order code: T1200TB25A ( $V_{CES} = 2500V$ )			

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